

(b) Amendments to the Claims

Please cancel claims 9 and 56 without prejudice or disclaimer. Please amend claims 1-5, 8 and 11 as follows. A detailed listing of all the claims that are or were on the application is provided.

--1. (Currently Amended) Process for decomposing powdery by-product and residual non-reacted gas comprising silicon or a compound thereof as a main component formed during processing a silicon-based amorphous or microcrystalline substrate or film comprising: An exhaust processing process of a processing apparatus for processing a substrate or a film, comprising the steps of:

(a) during after processing a the substrate or a the film exhausting the unreacted gas and the powdery by-product, introducing a non-reacted gas and/or a by-product comprising silicon or a compound thereof as a main component into a trap means having therein a filament comprising a high-melting metal material comprising as a main component at least one of tungsten, molybdenum or and rhenium; and

(b) decomposing the non-reacted gas and the powdery by-product by heating the filament to a temperature from 1400°C to 2200°C[[:] and, whereby adherence of the powdery by-product to the trap means is reduced without compromising the integrity of the filament and vacuum seals around the trap processing the non-reacted gas and/or the by-product inside the trap means.

2. (Currently Amended) The ~~exhaust processing~~ process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film is formed on the substrate by a plasma CVD process.

3. (Currently Amended) The ~~exhaust processing~~ process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film is formed on the substrate by a thermal CVD process.

4. (Currently Amended) The ~~exhaust processing~~ process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film is formed on the substrate by a photo CVD process.

5. (Currently Amended) The ~~exhaust processing~~ process according to claim 1, wherein the processing apparatus is an apparatus for processing the film is processed by a dry etching process.

6. and 7. (Cancelled)

8. (Currently Amended) The ~~exhaust processing~~ process according to claim 1, wherein the configuration of the filament comprises a single linear shape, a plurality of linear shapes or a linear shape wound in spirals.

9. and 10. (Cancelled)

11. (Currently Amended) The ~~exhaust~~ processing process according to  
claim 1, wherein a wall surface of the trap is of a double structure, and an inner wall  
surface is detachable.

12. - 56. (Cancelled)